

T. 33-19

File Number 676

2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

Epitaxial-Base, Silicon N-P-N and P-N-P VERSAWATT Transistors

General-Purpose Medium-Power Types for Switching and Amplifier Applications

Features:

- Low saturation voltages
- Complementary n-p-n and p-n-p types
- Maximum safe-area-of-operation curves specified for dc operation

The RCA-2N6106-2N6111, 2N6288-2N6293, and 2N6473-2N6476 are epitaxial-base silicon transistors supplied in a VERSAWATT package. The 2N6288-2N6293, 2N6473, and 2N6474* are n-p-n complements of p-n-p types 2N6106-2N6111, 2N6475, and 2N6476[‡], respectively. All these transistors are intended for a wide variety of medium-power switching and amplifier applications, such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.

The 2N6289, 2N6291, and 2N6293 n-p-n types and 2N6106, 2N6108, and 2N6110 p-n-p devices fit into TO-213AA sockets. The remaining types are supplied in the JEDEC TO-220AB straight-lead version of the VERSAWATT package. All of these devices are also available on special order in a variety of lead-form configurations.

*Formerly RCA Dev. Nos. TA7784, TA8323, TA7783, TA8232, TA7782, TA8231, TA8444, and TA8723, respectively.
[‡]Formerly RCA Dev. Nos. TA8210, TA7741, TA8211, TA7742, TA8212, TA7743, TA8445, and TA8722, respectively.

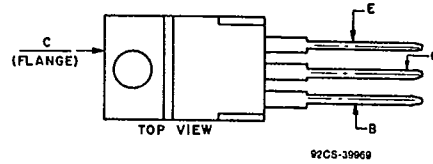
MAXIMUM RATINGS, Absolute-Maximum Values:

	2N6288		2N6290		2N6292		2N6473	2N6474
	N-P-N	2N6289	2N6291	2N6293	2N6293	2N6293		
	P-N-P	2N6110 [‡] 2N6111 [‡]	2N6108 [‡] 2N6109 [‡]	2N6106 [‡] 2N6107 [‡]	2N6475 [‡]	2N6476 [‡]		
V _{CEO}		40	60	80	110	130		V
V _{CEX(SUS)} R _{BB} = 100 Ω, V _{EB} = 0 V		40	60	80	110	130		V
V _{CEO(SUS)}		30	50	70	100	120		V
V _{EB0}				5				V
I _C (T _C ≤ 106° C)			7			4		A
I _E (T _C ≤ 130° C)			3			2		A
P _T								
T _C ≤ 25° C				40				W
T _C > 25° C ≤ 100° C				16				W
T _C > 25° C				Derate linearly 0.32				W/°C
T _A ≤ 25° C				1.8				W
T _A > 25° C				Derate linearly 0.0144				W/°C
T _{stg} , T _J				-65 to 150				°C
T _L								
At distances ≥ 1/8 in. (3.17 mm) from case for 10 s max.				235				°C

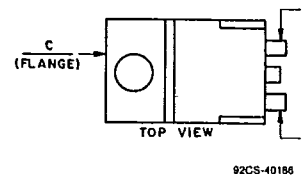
[‡]In accordance with JEDEC registration data.

[‡]For p-n-p devices, voltage and current values are negative.

TERMINAL DESIGNATIONS



JEDEC TO-220AB



JEDEC TO-220AA

3875081 G E SOLID STATE

01E 17416

D T-33-11

General-Purpose Power Transistors

T-33-19

2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

ELECTRICAL CHARACTERISTICS At Case Temperature (T_C) = 25°C Unless Otherwise Specified

CHARACTERISTIC	TEST CONDITIONS ^a				LIMITS						UNITS
	VOLTAGE V dc		CURRENT A dc		2N6292 2N6293 2N6106 [♦] 2N6107 [♦]		2N6290 2N6291 2N6108 [♦] 2N6109 [♦]		2N6288 2N6289 2N6110 [♦] 2N6111 [♦]		
	V _{CE}	V _{BE}	I _C	I _B	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
I _{CER} (R _{BE} = 100 Ω)	75				-	0.1	-	-	-	-	mA
	55				-	-	-	0.1	-	-	
	35				-	-	-	-	-	0.1	
(R _{BE} = 100 Ω, T _C = 150°C)	70				-	2	-	-	-	-	2
	50				-	-	-	2	-	-	
	30				-	-	-	-	-	-	
* I _{CEX} (R _{BE} = 100 Ω)	75	-1.5			-	0.1	-	-	-	-	mA
	56	-1.5			-	-	-	0.1	-	-	
	37.5	-1.5			-	-	-	-	-	0.1	
(R _{BE} = 100 Ω, T _C = 150°C)	70	-1.5			-	2	-	-	-	-	2
	50	-1.5			-	-	-	2	-	-	
	30	-1.5			-	-	-	-	-	-	
* I _{CEO}	60			0	-	1	-	-	-	-	1
	40			0	-	-	-	1	-	-	
	20			0	-	-	-	-	-	-	
* I _{EBO}		-5	0		-	1	-	1	-	1	
* V _{CEO(sus)} ^b			0.1 ^a	0	70	-	50	-	30	-	V
V _{CER(sus)} ^b (R _{BE} = 100 Ω)			0.1 ^a		80	-	60	-	40	-	V
* h _{FE}	4		2 ^a		30	150	-	-	-	-	
	4		2.5 ^a		-	-	30	150	-	-	
	4		3 ^a		-	-	-	-	30	150	
	4		7 ^a		2.3	-	2.3	-	2.3	-	
* V _{BE}	4		2 ^a		-	1.5	-	-	-	-	V
	4		2.5 ^a		-	-	-	1.5	-	-	
	4		3 ^a		-	-	-	-	-	1.5	
	4		7 ^a		-	3	-	3	-	3	
* V _{CE(sat)}			2 ^a	0.2	-	1	-	-	-	-	
			2.5 ^a	0.25	-	-	-	1	-	-	
			3 ^a	0.3	-	-	-	-	-	1	
			7 ^a	3	-	3.5	-	3.5	-	3.5	
* h _{fe} (f = 1 MHz)	4		0.5		4	-	4	-	4	-	
	2N6288-93										
2N6106-11	-4		-0.5		10	-	10	-	10	-	
* h _{fe} (f = 50 kHz)	4		0.5		20	-	20	-	20	-	
f _T	4		0.5		10	-	10	-	10	-	MHz
	2N6288-93										
2N6106-11	-4		-0.5		10	-	10	-	10	-	
* C _{obo} (f = 1 MHz)	10 ^c		0		-	250	-	250	-	250	pF
R _{θJC}					-	3.125	-	3.125	-	3.125	C/W
R _{θJA}					-	70	-	70	-	70	C/W

^a In accordance with JEDEC registration data.

^b Pulsed: Pulse duration = 300 μs, duty factor = 0.018.

^c CAUTION: The sustaining voltage V_{CEO(sus)} and V_{CER(sus)} MUST NOT be measured on a curve tracer.

^d V_{CB} value.

^e For p-n-p devices, voltage and current values are negative.

3875081 G E SOLID STATE

01E 17417 D T-33-11
General-Purpose Power Transistors

2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

ELECTRICAL CHARACTERISTICS At Case Temperature (T_C) = 25°C Unless Otherwise Specified

T-33-19

CHARACTERISTIC	TEST CONDITIONS				LIMITS				UNITS
	VOLTAGE V dc		CURRENT A dc		2N6474 2N6476*		2N6473 2N6475*		
	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	Min.	Max.	
I _{CER} (R _{BE} = 100 Ω)	120				-	0.1	-	-	mA
	100				-	-	-	0.1	
(R _{BE} = 100 Ω T _C = 100°C)	120				-	2	-	-	
	100				-	-	-	2	
* I _{CEX} (R _{BE} = 100 Ω)	120	-1.5			-	0.1	-	-	
	100	-1.5			-	-	-	0.1	
(R _{BE} = 100 Ω, T _C = 100°C)	120	-1.5			-	2	-	-	
	100	-1.5			-	-	-	2	
* I _{CEO}	60			0	-	1	-	-	
	50			0	-	-	-	1	
* I _{EBO}		-5		0	-	1	-	1	
* V _{CEO(sus)} ^b			0.1 ^a	0	120	-	100	-	V
V _{CER(sus)} ^b (R _{BE} = 100 Ω)			0.1 ^a		130	-	110	-	
* h _{FE}	4		1.5 ^a		15	150	15	150	
	2.5		4 ^a		2	-	2	-	
* V _{BE}	4		1.5 ^a		-	2	-	2	V
	2.5		4 ^a		-	3.5	-	3.5	
* V _{CE(sat)}			1.5 ^a	0.15	-	1.2	-	1.2	
			4 ^a	2	-	2.5	-	2.5	
* h _{fe} (f = 1 MHz) 2N6473-74	4		0.5		4	-	4	-	MHz
	-4		-0.5		5	-	5	-	
* h _{fe} (f = 50 kHz)	4		0.5		20	-	20	-	
	-4		-0.5		5	-	4	-	
* f _T 2N6473-74	4		0.5		4	-	4	-	
	-4		-0.5		5	-	4	-	
* C _{obo} (f = 1 MHz)	10 ^c		0		-	250	-	250	pF
R _{θJC}					-	3.125	-	3.125	°C/W
R _{θJA}					-	70	-	70	

* In accordance with JEDEC registration data

^a Pulsed: Pulse duration = 300 μs, duty factor = 0.018.

^b CAUTION: The sustaining voltage V_{CEO(sus)} are V_{CER(sus)} MUST NOT be measured on a curve tracer.

^c V_{CB} value.

♦ For p-n-p devices, voltage and current values are negative.

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General-Purpose Power Transistors

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2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

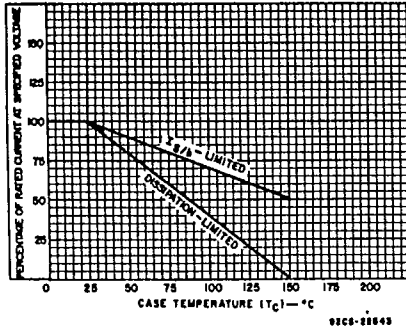


Fig. 1 - Current derating curves for all types.

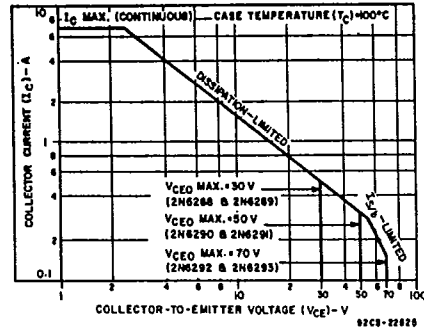


Fig. 2 - Maximum operating areas for 2N6288 - 2N6293 ($T_C = 100^\circ C$).

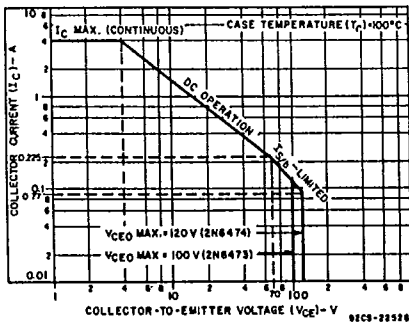


Fig. 3 - Maximum operating areas for 2N6473 - 2N6474 ($T_C = 100^\circ C$).

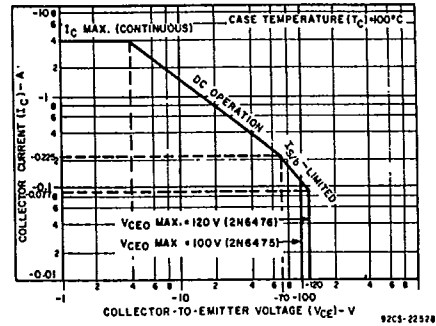


Fig. 4 - Maximum operating areas for 2N6475 and 2N6476 ($T_C = 100^\circ C$).

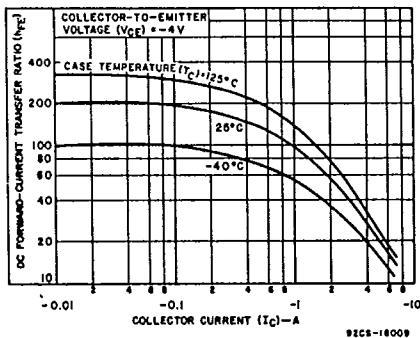


Fig. 5 - Typical dc beta characteristics for 2N6106 - 2N6111.

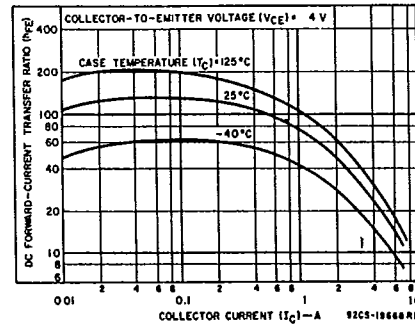


Fig. 6 - Typical dc beta characteristics for 2N6288 - 2N6293.

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General-Purpose Power Transistors

2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

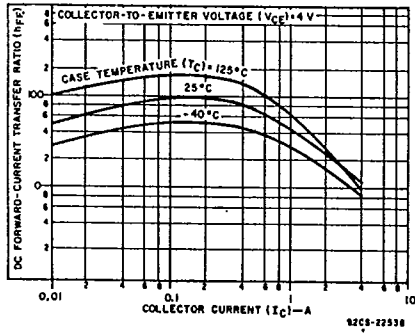


Fig. 7 - Typical dc beta characteristics for 2N6473 and 2N6474.

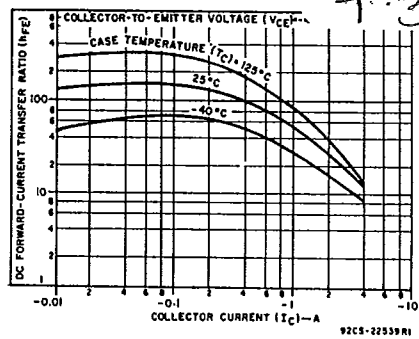


Fig. 8 - Typical dc beta characteristics for 2N6475 and 2N6476.

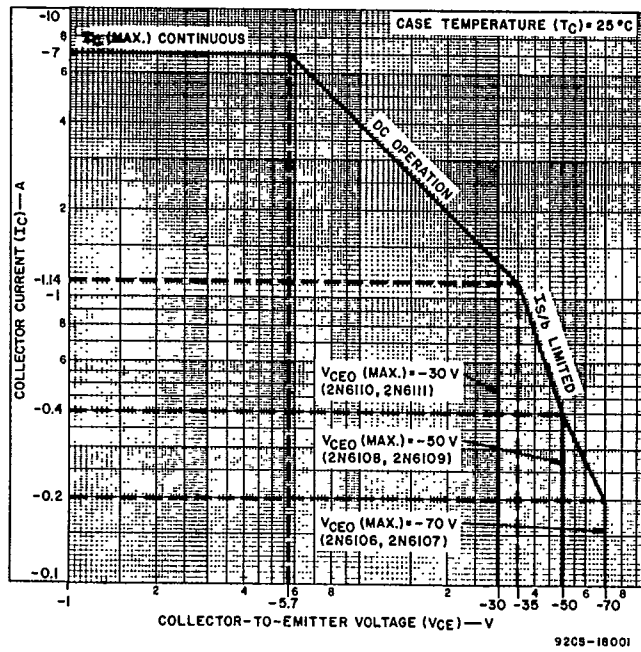


Fig. 9 - Maximum operating areas for 2N6106 - 2N6111 ($T_C = 25^\circ\text{C}$).

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General-Purpose Power Transistors

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2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

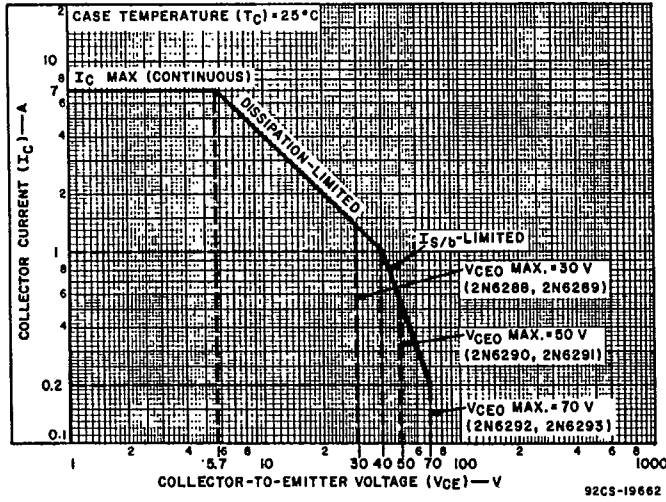


Fig. 10 - Maximum operating areas for 2N6288-2N6293 ($T_C = 25^\circ C$).

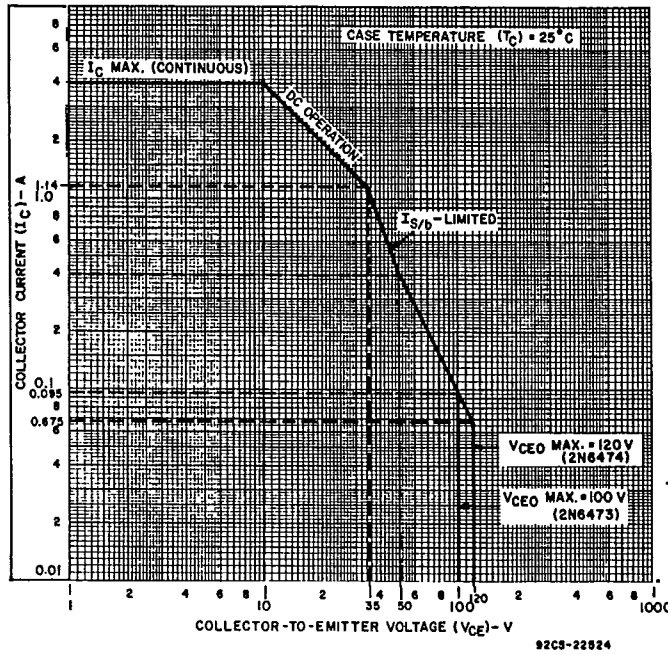


Fig. 11 - Maximum operating areas for 2N6473 and 2N6474 ($T_C = 25^\circ C$).

2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

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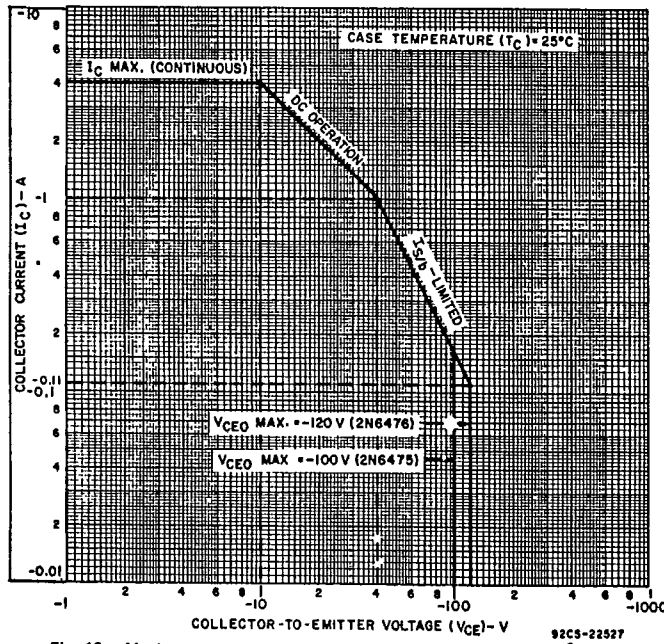


Fig. 12 - Maximum operating areas for 2N6475 - 2N6476 ($T_c = 25^\circ C$).

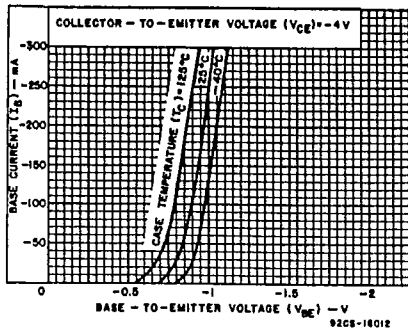


Fig. 13 - Typical input characteristics for 2N6106 - 2N6111, 2N6475, and 2N6476.

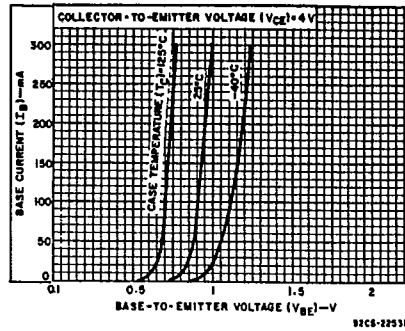


Fig. 14 - Typical input characteristics for 2N6288 - 2N6293.

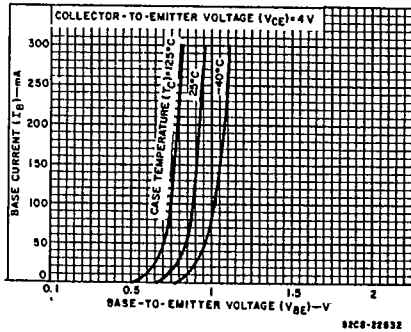


Fig. 15 - Typical input characteristics for 2N6473 - 2N6474.

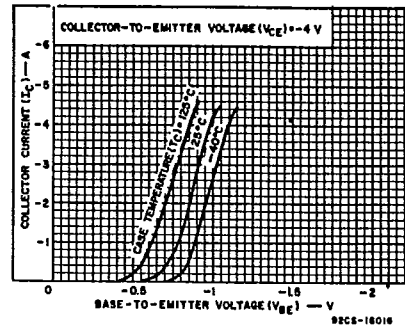


Fig. 16 - Typical transfer characteristics for 2N6106 - 2N6111.

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General-Purpose Power Transistors

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2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

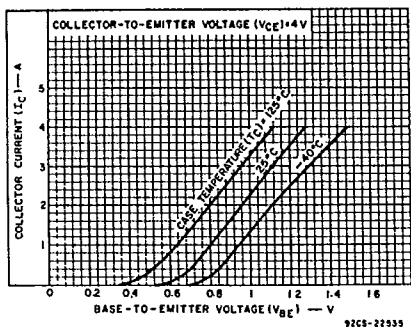


Fig. 17 - Typical transfer characteristics for 2N6288 - 2N6293.

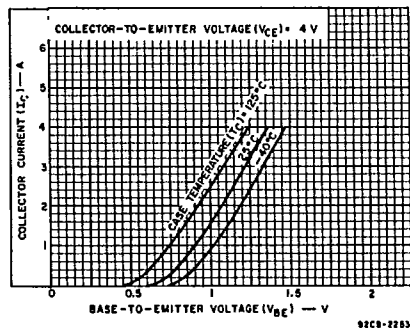


Fig. 18 - Typical transfer characteristics for 2N6473 and 2N6474.

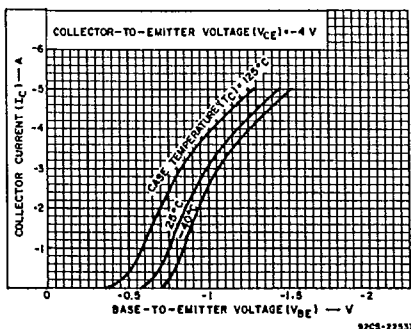


Fig. 19 - Typical transfer characteristics for 2N6475 and 2N6476.

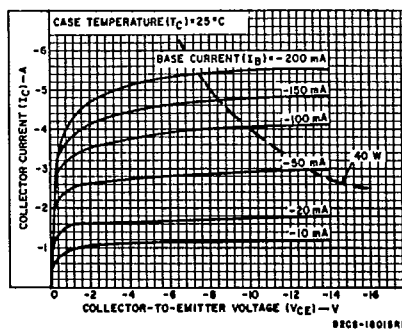


Fig. 20 - Typical output characteristics for 2N6106 - 2N6111.

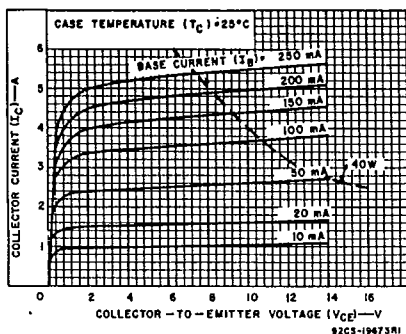


Fig. 21 - Typical output characteristics for 2N6288 - 2N6293.

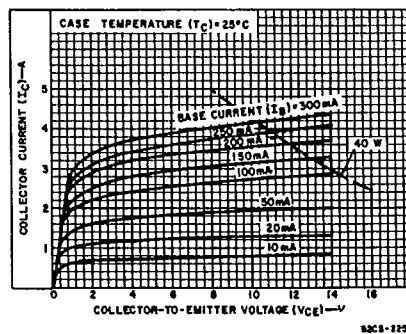


Fig. 22 - Typical output characteristics for 2N6473 and 2N6474.

2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

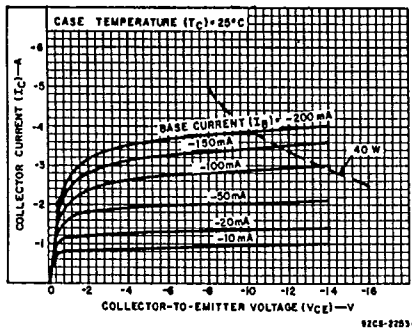


Fig. 23 - Typical output characteristics for 2N6475 and 2N6476.

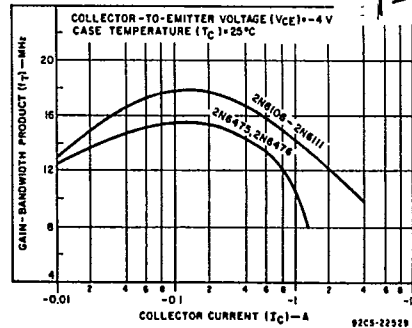


Fig. 24 - Typical gain-bandwidth product 2N6106 - 2N6111, 2N6475, and 2N6476.

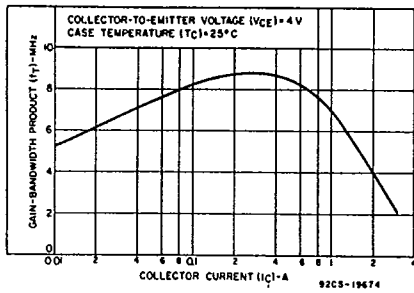


Fig. 25 - Typical gain-bandwidth product for 2N6288 - 2N6293.

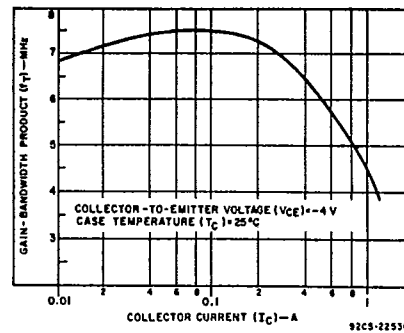


Fig. 26 - Typical gain-bandwidth product for 2N6473 and 2N6474.

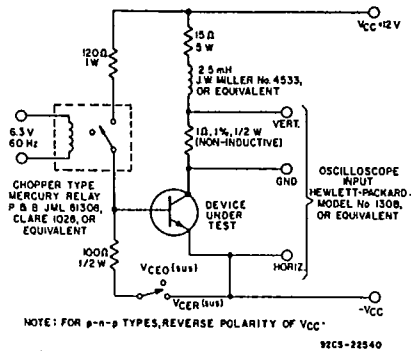
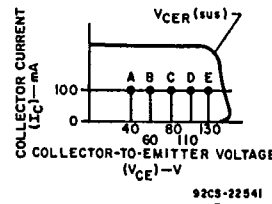


Fig. 27 - Circuit used to measure sustaining voltage $V_{CE R}(sus)$ for all types.



Note: Curve will be inverted and polarity reversed for p-n-p types. The sustaining voltage, $V_{CE R}(sus)$, is acceptable when the traces fall to the right and above the designated points:
Point A: 2N6110, 2N6111, 2N6288, 2N6289
Point B: 2N6108, 2N6109, 2N6290, 2N6291
Point C: 2N6106, 2N6107, 2N6292, 2N6293
Point D: 2N6475, 2N6473
Point E: 2N6476, 2N6474

Fig. 28 - Oscilloscope delay for measurement of sustaining voltage (test circuit shown in Fig. 27).

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